

Refine Search

Search Results -

Terms	Documents
L6 and DRAM	920

Database:

US Pre-Grant Publication Full-Text Database
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Search:

L7

Search History

DATE: Wednesday, February 15, 2006 [Printable Copy](#) [Create Case](#)

Set Name Query

side by side

Hit Count Set Name

result set

DB=USPT; PLUR=YES; OP=OR

L7 L6 and DRAM 920 L7

L6 "embedded memory" 1974 L6

DB=PGPB; PLUR=YES; OP=OR

L5 "embedded memory" 1759 L5

L4 L3 and processor 1 L4

L3 L2 AND "28" 1 L3

L2 L1 AND "INSULATING REGION" 1 L2

L1 20060022302 1 L1

END OF SEARCH HISTORY

Refine Search

Search Results -

Terms	Documents
DRAM same (capacit\$5 near10 (dielectric) near7 (aluminum near5 oxide))	7

Database:

US Pre-Grant Publication Full-Text Database
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Search:

L19

Search History

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<u>Set</u> <u>Name</u> side by side	<u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
	<i>DB=USPT; PLUR=YES; OP=OR</i>		
<u>L19</u>	DRAM same (capacit\$5 near10 (dielectric) near7 (aluminum near5 oxide))	7	<u>L19</u>
<u>L18</u>	DRAM same (capacit\$5 near6 (dielectric) near7 "metal-semiconductor")	0	<u>L18</u>
<u>L17</u>	Dram and (monocrystalline near4 ((electrode or plate) near3 capacitor))	9	<u>L17</u>
<u>L16</u>	Dram and (monocrystalline near6 ((electrode or plate) near3 capacitor))	22	<u>L16</u>
<u>L15</u>	Dram and (monocrystalline near10 ((electrode or plate) near5 capacitor))	35	<u>L15</u>
<u>L14</u>	Dram and (monocrystalline near10 capacitor)	88	<u>L14</u>
<u>L13</u>	Dram and (monocrystalline near10 capacitor)	0	<u>L13</u>
<u>L12</u>	L8 and monocrystal\$6	2	<u>L12</u>

DB=PGPB; PLUR=YES; OP=OR

<u>L11</u>	L1 and "auxiliary doping"	1	<u>L11</u>
<u>L10</u>	L1 and "auxiliary doping"	0	<u>L10</u>
<u>L9</u>	L1 and auxiliary	1	<u>L9</u>

DB=USPT; PLUR=YES; OP=OR

<u>L8</u>	DRAM and (tft same "storage capacitor" same substrate)	23	<u>L8</u>
<u>L7</u>	L6 and DRAM	920	<u>L7</u>
<u>L6</u>	"embedded memory"	1974	<u>L6</u>

DB=PGPB; PLUR=YES; OP=OR

<u>L5</u>	"embedded memory"	1759	<u>L5</u>
<u>L4</u>	L3 and processor	1	<u>L4</u>
<u>L3</u>	L2 AND "28"	1	<u>L3</u>
<u>L2</u>	L1 AND "INSULATING REGION"	1	<u>L2</u>
<u>L1</u>	20060022302	1	<u>L1</u>

END OF SEARCH HISTORY